

ABSTRACT OF THE DISCLOSURE

In a thin film transistor provided with a metallic layer with a light-shading property and a Si layer formed on an insulating layer, a dent for locally thinning the insulating layer is formed on a portion corresponding to a drain region. When the Si layer is recrystallized by means of a laser light irradiation, the dent serves as a crystalline nucleus formation region in order to recrystallize a particular portion earlier than other portions. Recrystallization of melted Si starts from a periphery of a bottom surface of the dent, hence a Si layer formed of a single crystal or uniformed crystal grains which serves as an active region of the TFT can be obtained.